

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP02525F uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS}(\text{ON})}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

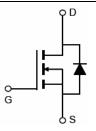
General Features

- V_{DS} =250V, I_D =25A $R_{DS(ON)}$ =60m Ω (typical) @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!



Schematic diagram



Marking and pin assignment



TO-220F top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02525F	NCEP02525F	TO-220F	-	-	-

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	250	V	
Gate-Source Voltage	V _{GS}	±20	V	
Drain Current-Continuous	I _D	25	Α	
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	17.5	А	
Pulsed Drain Current	I _{DM}	100	А	
Maximum Power Dissipation	P _D	45	W	
Derating factor		0.3	W/℃	
Single pulse avalanche energy (Note 5)	E _{AS}	320	mJ	
Operating Junction and Storage Temperature Range	T_{J},T_{STG}	-55 To 175	°C	

Thermal Characteristic

Thermal Résistance, Junction-to-Case ^(Note 2)	R _{eJC}	3.3	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Symbol Condition		Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA 250		-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =250V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5	3.5	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	60	70	mΩ
Forward Transconductance	G FS	V _{DS} =5V,I _D =20A	15	-	-	S
Dynamic Characteristics (Note4)	·					
Input Capacitance	C _{lss}	V _{DS} =125V,V _{GS} =0V,	-	1600		PF
Output Capacitance	C _{oss}	V _{DS} =125V,V _{GS} =0V, F=1.0MHz	-	92		PF
Reverse Transfer Capacitance	C _{rss}	Γ-1.UIVIΠZ	-	4.3		PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t _{d(on)}		-	7	-	nS
Turn-on Rise Time	t _r	V_{DD} =125 V , R_L =7.5 Ω	-	9	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	25	-	nS
Turn-Off Fall Time	t _f		-	5	ī	nS
Total Gate Charge	Qg	V -125V/I -20A	-	24	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =125V, I_{D} =20A, V_{GS} =10V	-	9.5	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	5.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	25	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S	-	45	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	160	ì	nC

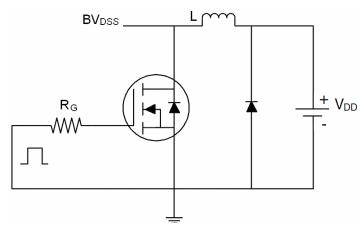
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω

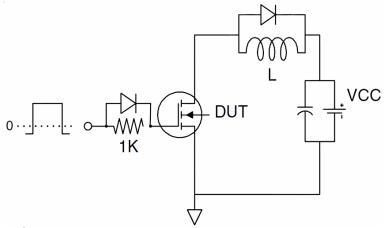


Test Circuit

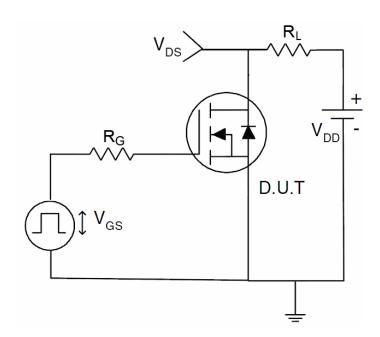
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

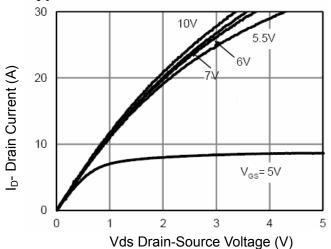


Figure 1 Output Characteristics

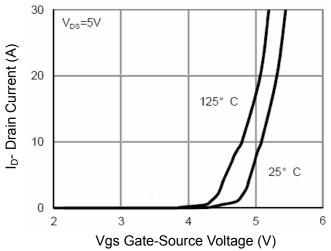


Figure 2 Transfer Characteristics

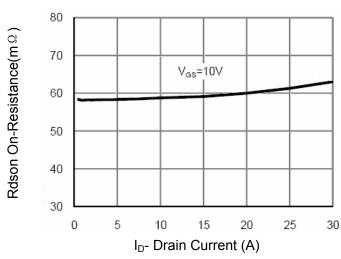


Figure 3 Rdson- Drain Current

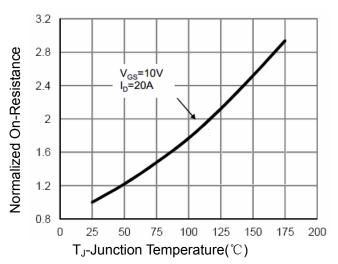


Figure 4 Rdson-Junction Temperature

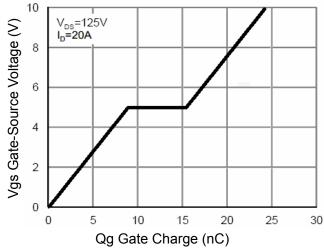


Figure 5 Gate Charge

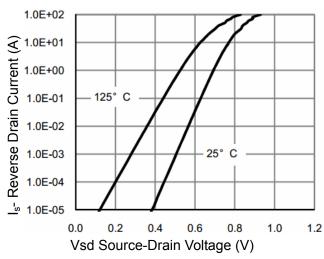
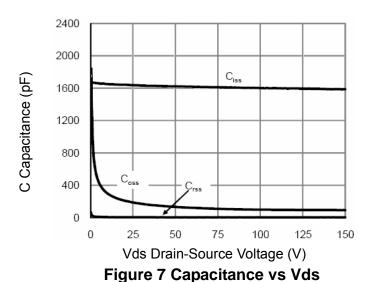
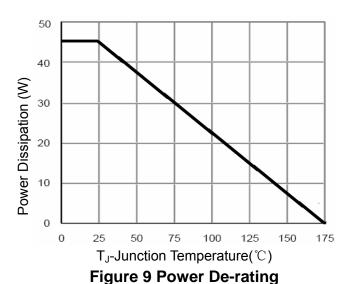


Figure 6 Source- Drain Diode Forward







100.0 10.0 00μs lp- Drain Current (A) R_{DS(ON)} limited 1.0 0ms DC 0.1 T_{J(Max)}=175° C T_C=25° C 0.0 0.01 100 1000 Vds Drain-Source Voltage (V)



Figure 8 Safe Operation Area



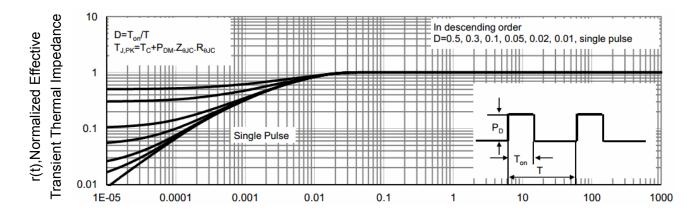
100

125

150

175

75



0

0

25

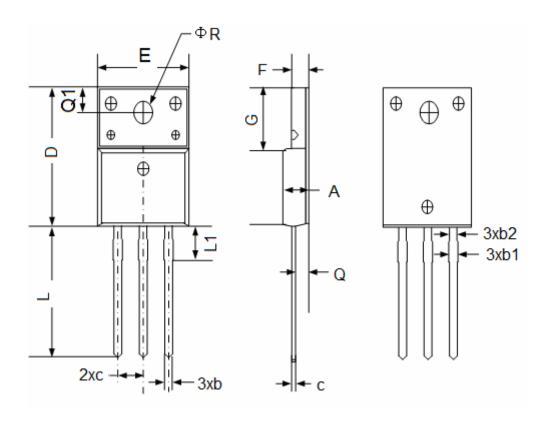
50

Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-220F Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.50	4.83	0.18	0. 19	
b	0.70	0.91	0.03	0.04	
b1	1.20	1.47	0.05	0.06	
b2	1.10	1.38	0.04	0.05	
С	0.45	0.63	0. 02	0.02	
D	15.67	16.07	0.62	0.63	
е	2.54	BSC	0.10 BSC		
Е	9.96	10.36	0. 39	0.41	
F	2.34	2.74	0.09	0. 11	
G	6.48	6.90	0. 26	0. 27	
L	12.68	13.30	0. 50	0. 52	
L1	3.13	3.50	0. 12	0.14	
Q	2.56	2.93	0. 10	0. 12	
Q1	3.20	3.40	0. 13	0. 13	
ΦR	3.08	3.28	0. 12	0. 13	



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